Photocouplers Infrared LED & Photo IC

TLP5212

1. Applications

- IGBT Gate Drivers
- MOSFET Gate Drivers
- Industrial Inverters
- AC Servos
- Photovoltaic (PV) Power Conditioning Systems
- Air Conditioner Inverters

2. General

The TLP5212 is a highly integrated 2.5 A output current IGBT gate drive photocoupler housed in a long creepage and clearance SO16L package.

The TLP5212, a smart gate driver photocoupler, includes functions of IGBT desaturation detection, isolated fault status feedback, soft gate turn-off, active Miller cramping and under voltage lockout (UVLO).

The TLP5212 consists two infrared light-emitting diodes (LEDs) and two high-gain and high-speed Light-receiving IC chips. They realize the control of output current and the feedback function of the fault signal with electrical isolation between a primary side and secondary side.

3. Features

(1) Peak output current : ± 2.5 A (max)
(2) Guaranteed performance over temperature : - 40 to 110 ℃
(3) Power supply voltage : 15 V to 30 V
(4) Threshold input current : 6 mA (max)
(5) Supply current : 5 mA (max)
(6) Propagation delay time : 250 ns (max)
(7) DESAT leading edge blanking time : 1.27 μs (typ)
(8) Common-mode transient immunity : ± 25 kV/μs (min)
(9) Isolation voltage : 5000 Vrms (min)
(10) Safety standards

UL approved	: UL1577, File No. E67349
cUL approved	: CSA Component Acceptance Service No.5A File No. E67349
VDE approved	: EN60747-5-5 (Note 1)
CQC approved	: GB4943.1, GB8898 Japan Factory



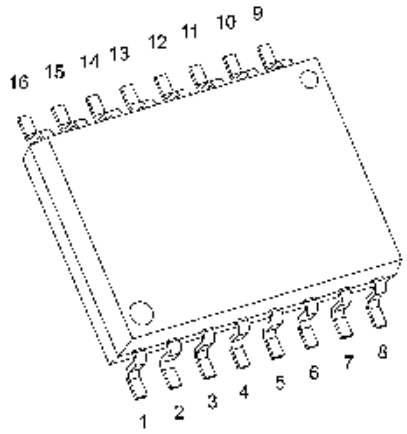
仅适用于海拔 2000m 以下地区安全使用

Note 1: When a VDE approved type is needed, please designate the Option (D4).

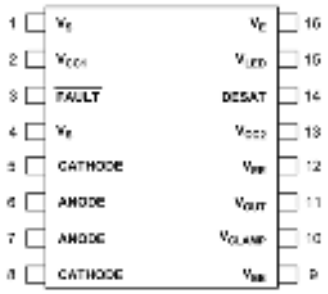
Start of commercial production
2022-04

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4. Packaging and Pin Assignment



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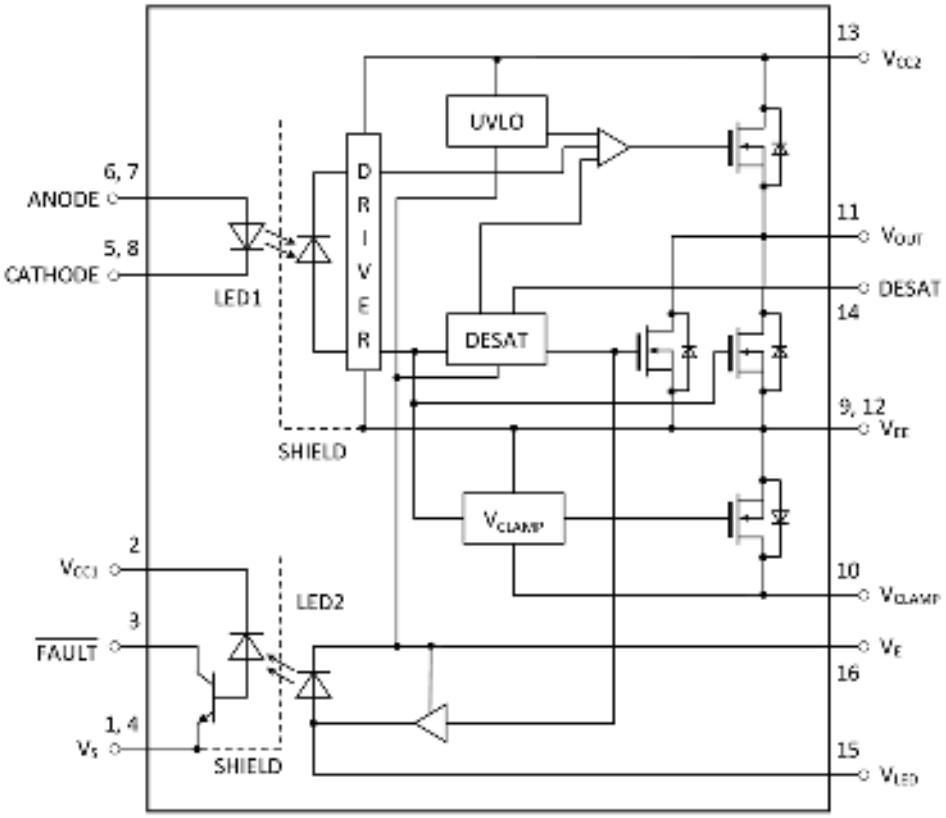


4.1. Pin Description

Pin No.	Symbol	Description
1	V_S	Input side ground
2	V_{CC1}	Positive input supply voltage. (2.7 V to 5.5 V)
3	$\overline{FAULT}$	Fault output
4	V_S	Input side ground
5	CATHODE	Input side LED Cathode
6	ANODE	Input side LED Anode
7	ANODE	Input side LED Anode
8	CATHODE	Input side LED Cathode
9	V_{EE}	Negative output supply voltage
10	V_{CLAMP}	Miller current clamp
11	V_{OUT}	Gate drive voltage output
12	V_{EE}	Negative output supply voltage
13	V_{CC2}	Positive output supply voltage
14	DESAT	Desaturation voltage input
15	V_{LED}	Not connect, for testing only
16	V_E	Common (IGBT emitter) output supply voltage.

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5. Internal Circuit (Note)



Note : Bypass capacitors (1 μF) must be connected between pin 13 (V_{CC2}) and 16 (V_E) to stabilize the operation of the high gain linear amplifier. When $V_E - V_{EE} > 0$ V (with negative gate drive), another bypass capacitor (1 μF) must be connected between pin 9 or 12 (V_{EE}) and 16 (V_E). Failure to provide the bypassing may impair the switching property. The total lead length between each capacitor and the coupler should not exceed 1 cm.

6. Principle of Operation

6.1. Truth Table

Input Current I_F	Under Voltage Lock Out UVLO (V_{CC2} - V_E)	Over current protection DESAT (Pin14 input)	Feedback function $\overline{FAULT}$ (Pin3 output)	IGBT Gate voltage V_{OUT}
ON	Active (< V_{UVLO}^-)	Not Active	High	Low
ON	Not Active (> V_{UVLO}^+)	Active (with DESAT fault)	Low (FAULT)	Low
ON	Not Active (> V_{UVLO}^+)	Active (no DESAT fault)	High	High
OFF	Active (< V_{UVLO}^-)	Not Active	High	Low
OFF	Not Active (> V_{UVLO}^+)	Not Active	High	Low

6.2. Mechanical Parameters

Characteristics	Dimensions	Unit
Creepage distances	8.0 (min)	mm
Clearance distances		
Internal isolation thickness	0.4 (min)	

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7. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 ℃)

	Characteristics		Symbol	Note	RATING	Unit
LED & Feedback (controller side)	LED Input forward current		I_F		25	mA
	LED Input forward current derating (Ta ≥ 90°C)		$\Delta I_F/\Delta Ta$		-0.65	mA/°C
	Peak transient input LED forward current		I_{FPT}	Note 1	1	A
	LED Reverse input voltage		V_R		5	V
	FAULT feedback IC supply voltage		V_{CC1}		−0.5 to 7	V
	FAULT feedback output current		$I_{\overline{FAULT}}$		8	mA
	FAULT feedback output voltage		$V_{\overline{FAULT}}$		−0.5 to V_{CC1}	V
	Input LED power dissipation		P_D		60	mW
	Input LED power dissipation derating (Ta ≥ 90°C)		$\Delta P_D/\Delta Ta$		−1.9	mW/°C
Output (gate Driver side)	Peak high-level output current	Ta = −40 to 110 °C	I_{OPH}	Note 2 Note 3	-2.5	A
	Peak low-level output current		I_{OPL}		+2.5	A
	Total output side supply voltage		$(V_{CC2}-V_{EE})$		-0.5 to 35	V
	Negative output side supply voltage		(V_E-V_{EE})		-0.5 to 15	V
	Positive output side supply voltage		$(V_{CC2}-V_E)$		-0.5 to 35 − (V_E-V_{EE})	V
	Output voltage		V_{OUT}		V_{EE} to V_{CC2}	V
	Peak power device gate clamping sinking current		I_{Clamp}		2.5	A
	Miller clamping pin voltage		V_{Clamp}		V_{EE} to V_{CC2}	V
	DESAT pin voltage		V_{DESAT}		V_E to V_E + 10	V
	Output gate drive IC power dissipation		P_O	Note 3	600	mW
	P_O derating (Ta ≥90°C)		$\Delta P_O/\Delta Ta$	Note 3	-13.0	mW/°C
Common	Operating temperature range		T_{opr}		-40 ~ 110	°C
	Storage temperature range		T_{stg}		-55 ~ 125	°C
	Lead soldering temperature (10 s)		T_{sol}	Note 4	260	°C
	Isolation voltage (AC, 60 s, R.H. ≤ 60%)		BV_S	Note 5	5000	Vrms

Note : Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.)

Note 1: Pulse width ≤ 1 μs, 300 pps

Note 2: Exponential waveform. Pulse width ≤ 0.28 μs, f ≤ 25 kHz, V_{CC2} = 15 to 30 V

Note 3: Mounting on a substrate designated in accordance with JEDEC JESD51-7.

Note 4: For the effective lead soldering area.

Note 5: This device considered a two-terminal device: All pins on the LED side are shorted together, and all pins on the photodetector side are shorted together.

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8. Recommended Operation Conditions (Note)

Characteristics	Symbol	Note	Min	Max	Unit
Total output side supply voltage	(V_{CC2} - V_{EE})	Note 1 Note 2	15	30	V
Negative output side supply voltage	(V_E - V_{EE})	Note 1 Note 3	0	15	V
Positive output side supply voltage	(V_{CC2} - V_E)	Note 1 Note 2	15	30 - (V_E - V_{EE})	V
FAULT feedback IC supply voltage	V_{CC1}		2.7	5.5	V
LED Input on-state current	$I_{F(ON)}$	Note 4	7.5	12	mA
LED Input off-state voltage	$V_{F(OFF)}$		0	0.8	V

Note : The recommended operating conditions are given as a design guide necessary to obtain the intended performances of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

Note 1: If the rising slopes of V_{CC2} and V_{EE} are so steep, the internal circuit operation may not be stable. In that case, please design the slopes to be 0.5 V/μs or less.

Note 2: 15 V is the recommended minimum operating positive supply voltage (V_{CC2} - V_E) to ensure adequate margin in excess of the maximum V_{UVLO+} threshold of 12.5V.

Note 3: This supply is optional. Required only when negative gate drive is implemented.

Note 4: The rise and fall times of the input on-current should be less than 500 μs.

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9. Electrical Characteristics (Note)

(Unless otherwise specified, Ta = - 40 to 110 °C, V_{CC2} - V_{EE} = 15 to 30 V, V_E - V_{EE} = 0 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input forward voltage	V_F			I_F = 10 mA, Ta = 25 °C	1.48	1.67	1.93	V
Input reverse current	I_R			V_R = 5 V, Ta = 25 °C	–	–	10	μA
Input capacitance (between Pin 7 to 8)	C_t			V = 0 V, f = 1 MHz, Ta = 25 °C	–	20	–	pF
FAULT low level output voltage	$V_{\overline{FAULTL}}$			$I_{\overline{FAULT}}$ = 1.1 mA, V_{CC1} = 5.5 V	–	0.1	0.4	V
				$I_{\overline{FAULT}}$ = 1.1 mA, V_{CC1} = 2.7 V	–	0.1	0.4	
FAULT high level output current	$I_{\overline{FAULTH}}$			$V_{\overline{FAULT}}$ = V_{CC1} = 5.5 V, Ta = 25 °C	–	0.02	0.5	μA
				$V_{\overline{FAULT}}$ = V_{CC1} = 2.7 V, Ta = 25 °C	–	0.002	0.3	
High level output current	I_{OPH}	Note 1	13.1.1	V_{OUT} = V_{CC2} - 4 V	–	-2.9	-2.0	A
Low level output current	I_{OPL}	Note 1	13.1.2	V_{OUT} = V_{EE} + 2.5 V	2.0	3.1	–	
Low level output current during fault condition	I_{OLF}			V_{OUT} - V_{EE} = 14 V	90	180	230	mA
High level output voltage	V_{OH}		13.1.3	I_{OUT} = - 650 μA	V_{CC2}-2.9	V_{CC2}-1.6	–	V
Low level output voltage	V_{OL}		13.1.4	I_{OUT} = 100 mA	–	0.12	0.5	
Clamp pin threshold voltage	V_{tClamp}			I_{CL} = 100 mA	–	2.3	–	
Clamp low level sinking current	I_{CL}			V_{Clamp} = V_{EE} + 2.5 V	0.35	2.4	–	A
High level supply current	I_{CC2H}		13.1.5	I_F = 10 mA	–	3.2	5	mA
Low level supply current	I_{CC2L}		13.1.6	I_F = 0 mA	–	2.5	5	
Blanking capacitor charging current	I_{CHG}		13.1.7	I_F = 10 mA, V_{DESAT} = 2 V	-0.33	-0.26	-0.13	
Blanking capacitor discharging current	I_{DSCHG}		13.1.8	V_{DESAT} = 7 V	10	28.5	–	
DESAT threshold voltage	V_{DESAT}			I_F = 10 mA, I_{DESAT} > 0	6.0	6.6	7.5	V
UVLO threshold voltage	V_{UVLO}^+		13.1.9	I_F = 10 mA, V_{OUT} > 5 V	10.5	11.4	12.5	
	V_{UVLO}^-		13.1.9	I_F = 10 mA, V_{OUT} < 5 V	9.2	10.0	11.1	
UVLO hysteresis	$UVLO_{HYS}$			(V_{UVLO+} - V_{UVLO-})	0.4	1.4	–	
Threshold input current (L/H)	I_{FLH}		13.1.10	V_{CC2} = 30 V, V_{OUT} > 5 V	–	0.96	6	mA
Threshold input voltage (H/L)	V_{FHL}			V_{CC2} = 30 V, V_{OUT} < 5 V	0.8	–	–	V

Note : All typical values are at T_a = 25 °C.

Note 1: I_O application time ≤ 10 μs, single pulse

10. Isolation Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Note	Test conditions	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	Note 1	V_S = 0 V, f = 1 MHz	–	1.0	–	pF
Isolation resistance	R_S	Note 1	V_S = 500 V, R.H. ≤ 60 %	10^{12}	10^{14}	–	Ω
Isolation voltage	BV_S	Note 1	AC, 60 s	5000	–	–	Vrms

Note 1: This device considered a two-terminal device: All pins on the LED side are shorted together, and all pin on the Output side are shorted together.

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11. Switching Characteristics (Note)

(Unless otherwise specified, Ta = - 40 to 110 °C, V_{CC2} - V_{EE} = 15 to 30 V, V_E - V_{EE} = 0 V)

Characteristics		Symbol	Note	Test Circuit	Condition		Min	Typ.	Max	Unit
Propagation delay time	L→H	t_{pLH}	Note 1	13.1.11	R_g = 10 Ω, C_g = 10 nF, V_{CC2} = 30 V, f = 10 kHz, duty = 50 %	I_F = 0 → 10 mA	100	167	250	ns
	H→L	t_{pHL}				I_F = 10 → 0 mA	100	170	250	
Pulse width distortion		$\lvert t_{pHL}-t_{pLH} \rvert$				I_F = 10 ↔ 0 mA	–	3	50	
Propagation delay skew (device to device)		t_{psk}	Note 1 Note 2				-150	–	150	
Output rise time (10–90 %)		t_r	Note 1			I_F = 0 → 10 mA	–	57	–	
Output fall time (90–10 %)		t_f				I_F = 10 → 0 mA	–	56	–	
DESAT Sense to 90% V_{OUT} Delay		$t_{DESAT(90\%)}$		13.1.12	C_{DESAT} = 100 pF, R_g = 10 Ω, C_g = 10 nF, V_{CC2} = 30 V		–	147	500	ns
DESAT Sense to 10% V_{OUT} Delay		$t_{DESAT(10\%)}$					–	2	3	µs
DESAT leading edge blanking time		$t_{DESAT(LEB)}$					–	1.27	–	
DESAT filter time		$t_{DESAT(FILTER)}$					–	95	–	ns
DESAT Sense to DESAT Low Propagation Delay		$t_{DESAT(LOW)}$					–	172	–	
DESAT Sense to Low Level FAULT Signal Delay		$t_{DESAT(FAULT)}$			C_{DESAT} = 100 pF, R_g = 10 Ω, C_g = 10 nF, V_{CC2} = 30 V, V_{CC1} = 5 V	C_F = Open, R_F = 2.1 kΩ	–	343	500	ns
						C_F = 1 nF, R_F = 2.1 kΩ	–	644	–	
DESAT Input Mute		$t_{DESAT(MUTE)}$					5	-	–	µs
RESET to High Level FAULT Signal Delay		$t_{RESET(FAULT)}$			C_{DESAT} = 100 pF, R_g = 10 Ω, C_g = 10 nF, V_{CC2} = 30 V	V_{CC1} = 5.5 V, R_F = 2.1 kΩ	0.1	0.63	2.5	
						V_{CC1} = 3.3 V, R_F = 2.1 kΩ	0.1	0.65	2.5	
Output High Level Common Mode Transient Immunity		CM_H	Note 3	13.1.13, 13.1.14, 13.1.15, 13.1.16	Ta = 25 ℃ , V_{CM} = 1500 V_{P-P}, V_{CC2} = 30 V, R_F = 2.1 kΩ, R_g = 10 Ω, C_g = 10 nF	I_F = 10 mA, C_F = 15 pF	±25	±40	–	kV/µs
						I_F = 10 mA, C_F = 1 nF	±50	±100	–	
Output Low Level Common Mode Transient Immunity		CM_L	Note 4			V_F = 0 V, C_F = 15 pF	±25	±40	–	
						V_F = 0 V, C_F = 1 nF	±50	±100	–	

Note : All typical values are at T_a = 25 ℃. C_F is approximately 15 pF which includes probe and stray wiring capacitance.

Note 1: Input signal: f = 10 kHz, duty = 50 %, tr = tf = 5 ns or less

Note 2: The propagation delay skew, t_{psk}, is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

Note 3: Common mode transient immunity in the high state is the maximum tolerable dV_{CM}/dt of the common mode pulse, V_{CM}, to assure that the output will remain in the high state (V_{OUT} > 23 V, $V_{\overline{FAULT}}$ > 3 V).

Note 4: Common mode transient immunity in the low state is the maximum tolerable dV_{CM}/dt of the common mode pulse, V_{CM}, to assure that the output will remain in a low state (V_{OUT} < 1 V, $V_{\overline{FAULT}}$ < 2 V).

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12. Application Information

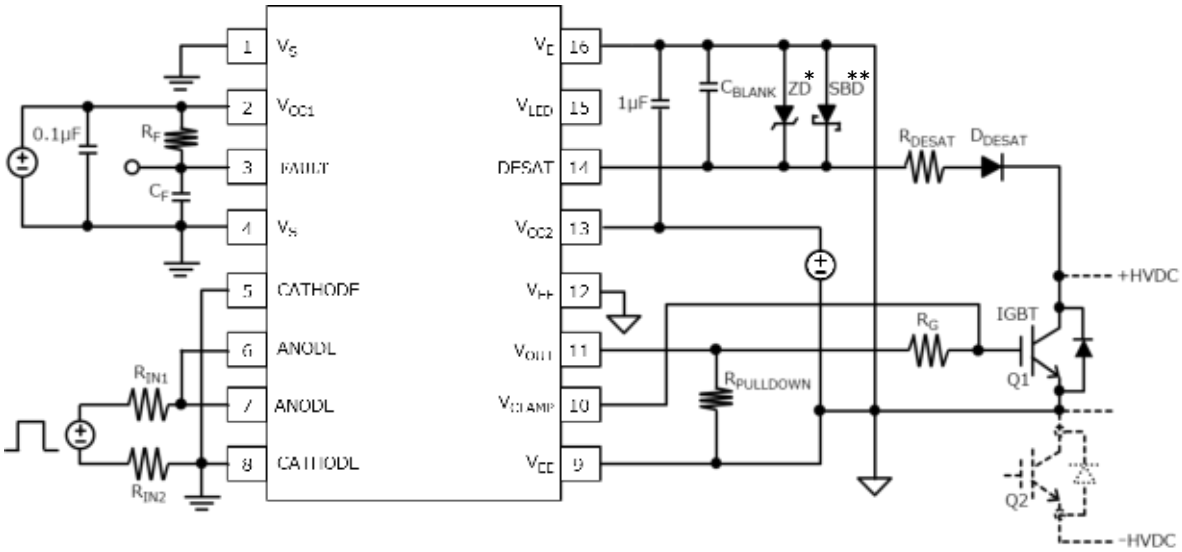


Fig 12.1 Recommended application circuit with positive gate drive, desaturation detection and active Miller Clamp

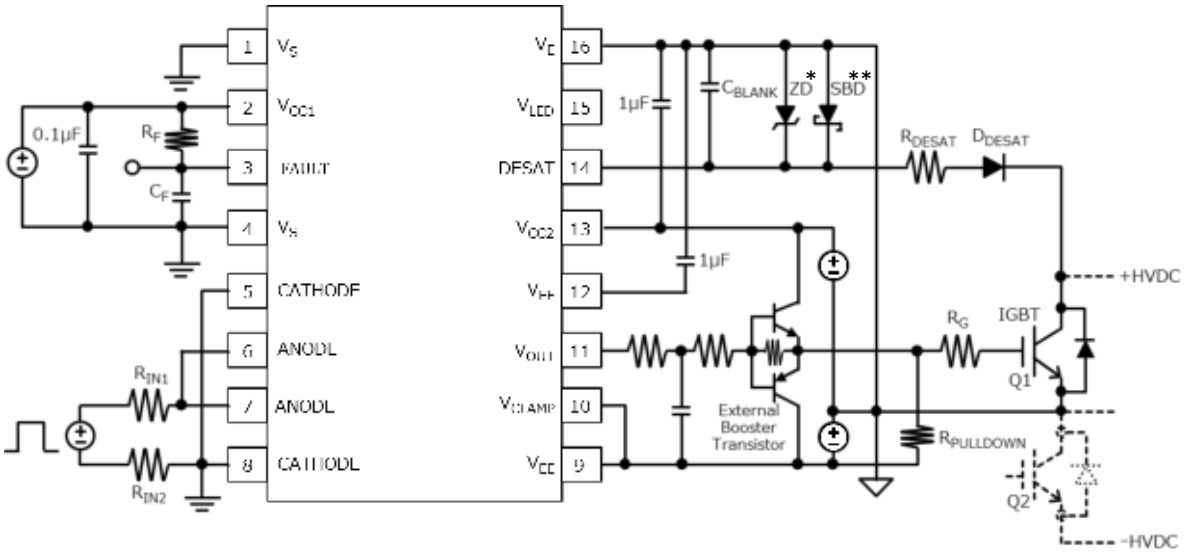


Fig 12.2 Recommended application circuit with negative gate drive, external booster transistors and desaturation detection

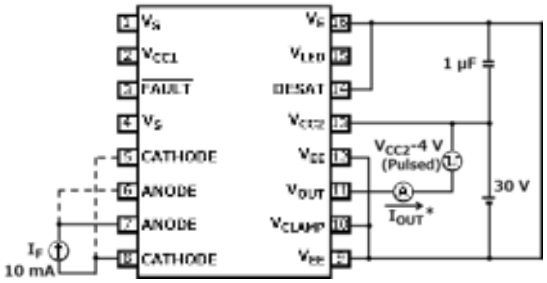
Note : Bypass capacitors (1 μF) must be connected between pin 13 (V_{CC2}) and 16 (V_E) to stabilize the operation of the high gain linear amplifier. When $V_E - V_{EE} > 0$ V (with negative gate drive), another bypass capacitor (1 μF) must be connected between pin 9 or 12 (V_{EE}) and 16 (V_E). Failure to provide the bypassing may impair the switching property. The total lead length between each capacitor and the coupler should not exceed 1 cm.
Refer to the connection of pin 14 and pin 16 for a desaturation detection function. The desaturation diode D_{DESAT} 600V / 1200V fast recovery type and capacitor C_{BLANK} are external components required for fault detection circuits. Also, select a resistance R_{DESAT} of 500 ohms or more for protection of DESAT pin 14. For details, refer to the application note "Smart Gate Driver Coupler Tips for Designing DESAT Detection Circuits".

＊ : Zener diode for DESAT pin protection. CUZ8V2 is recommended.
＊＊ : Schottky diode for DESAT false detection prevention. CUS05F30 is recommended.

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13. Reference Drawings

13.1. Test Circuits



* : The direction of the arrow indicates the actual current direction.

Fig. 13.1.1 I_{OPH} Test Circuit

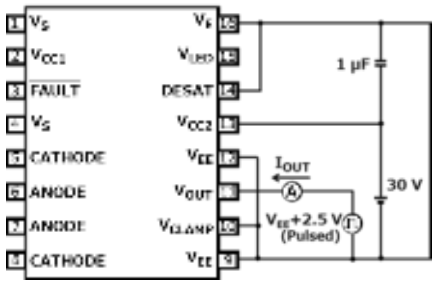
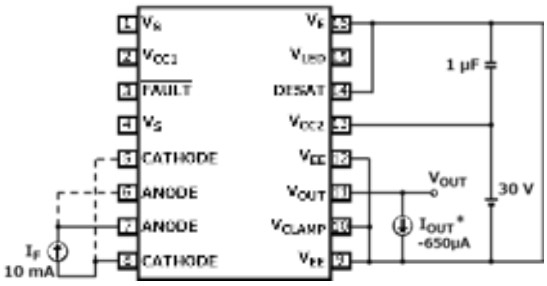


Fig. 13.1.2 I_{OPL} Test Circuit



* : The direction of the arrow indicates the actual current direction.

Fig. 13.1.3 V_{OH} Test Circuit

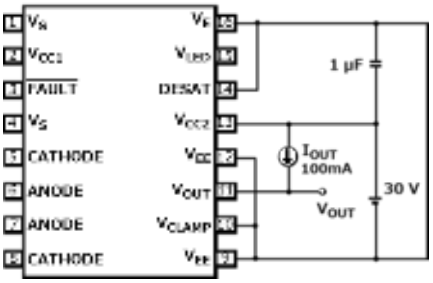


Fig. 13.1.4 V_{OL} Test Circuit

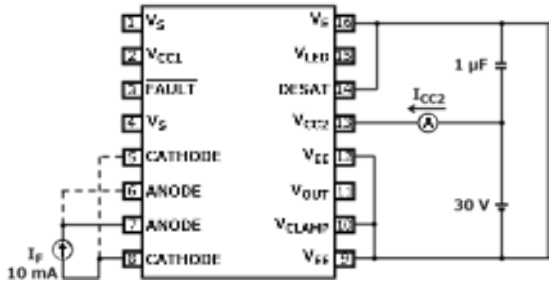


Fig. 13.1.5 I_{CC2H} Test Circuit

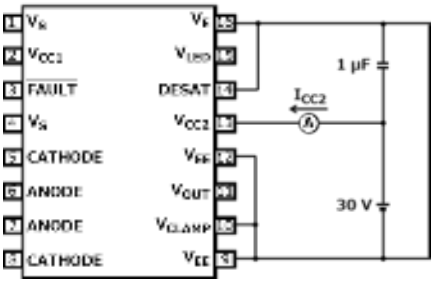
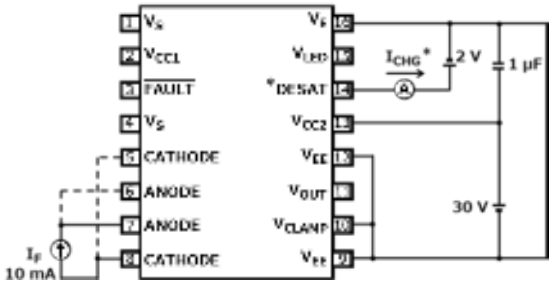


Fig. 13.1.6 I_{CC2L} Test Circuit

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* : It operates as a constant current circuit.
The direction of the arrow indicates the actual current direction.

Fig. 13.1.7 I_{CHG} Test Circuit

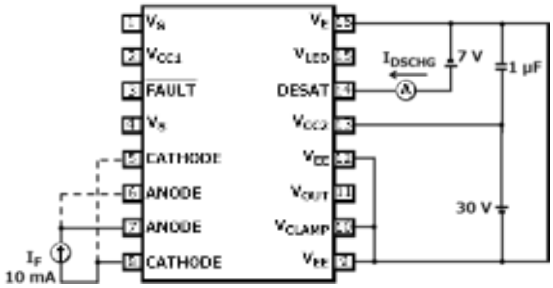


Fig. 13.1.8 I_{DSCHG} Test Circuit

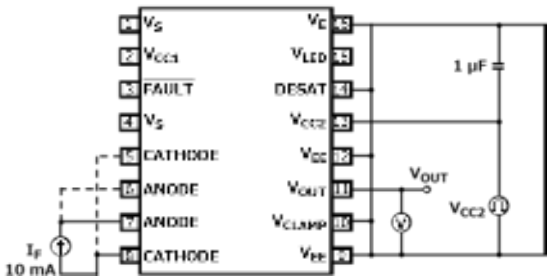


Fig. 13.1.9 V_{UVLO} Test Circuit

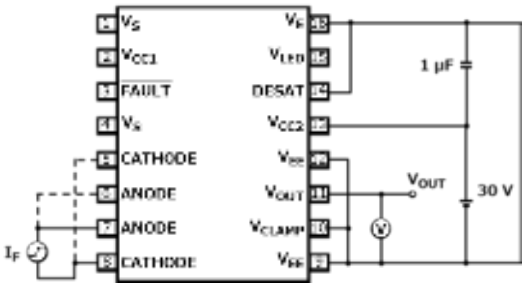
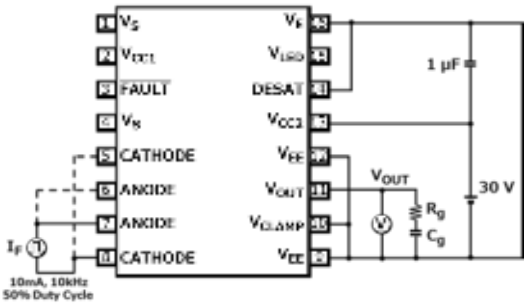


Fig. 13.1.10 I_{FLH} Test Circuit

I_F = 10 mA (P.G)
(f = 10 kHz, duty = 50 %, t_r = t_f = 5 ns or less)



P.G : Pulse Generator

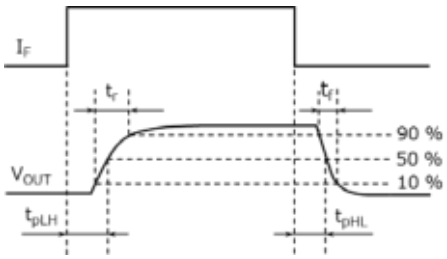
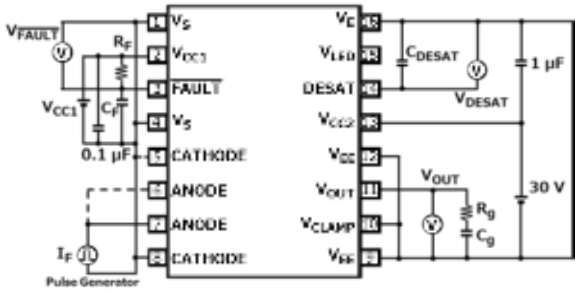


Fig 13.1.11 t_{pLH}, t_{pHL}, t_r, t_f, $|t_{pHL}-t_{pLH}|$ Test Circuit

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I_F = 10 mA (P.G)
(f = 10 kHz, duty = 50 %, t_r = t_f = 5 ns or less)



P.G : Pulse Generator

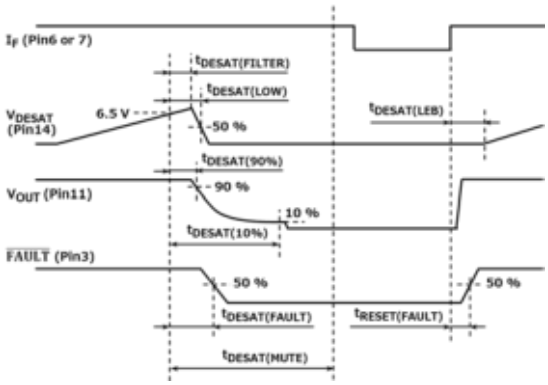


Fig 13.1.12 $t_{DESAT(90\%)}$, $t_{DESAT(10\%)}$, $t_{DESAT(FAULT)}$, $t_{DESAT(MUTE)}$, $t_{RESET(FAULT)}$ Test Circuit

V_{OUT} : High

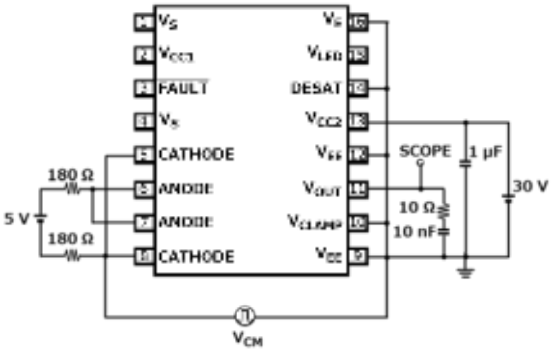


Fig 13.1.13 CMTI refer to V_E Test Circuit (LED1 on)

V_{OUT} : Low

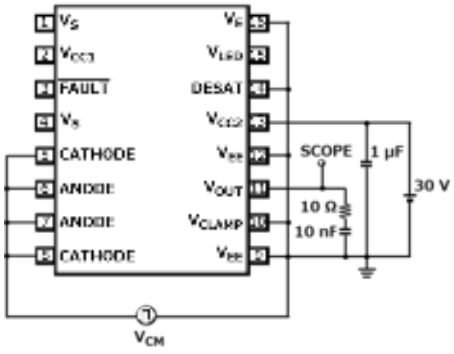


Fig 13.1.14 CMTI refer to V_E Test Circuit (LED1 off)

V_{FAULT} : Low

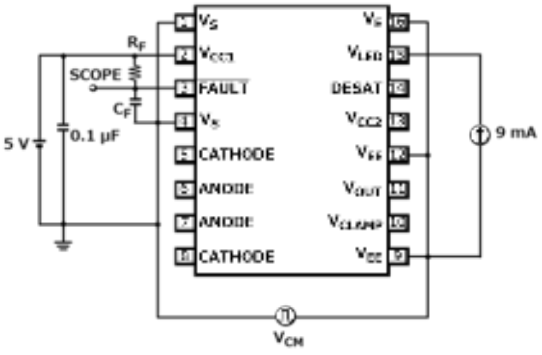


Fig 13.1.15 CMTI refer to V_S Test Circuit (LED2 on)

V_{FAULT} : High

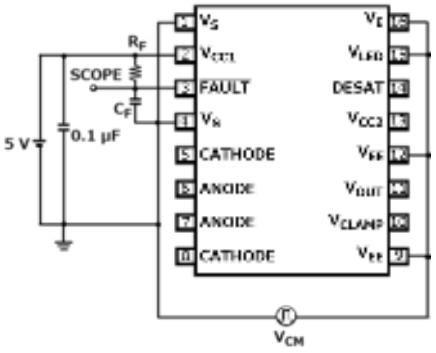


Fig 13.1.16 CMTI refer to V_S Test Circuit (LED2 off)

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13.2. Timing Chart

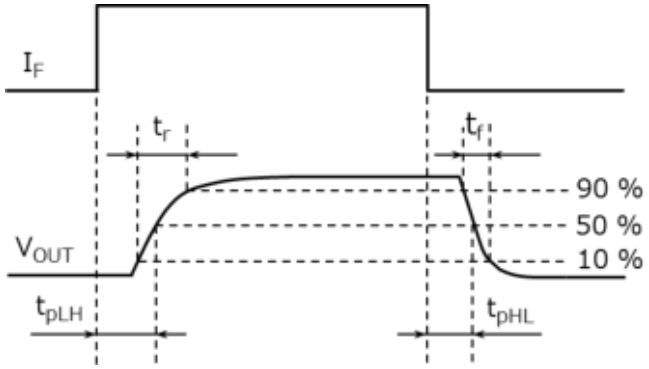


Fig 13.2.1 V_{OUT} propagation delay waveforms

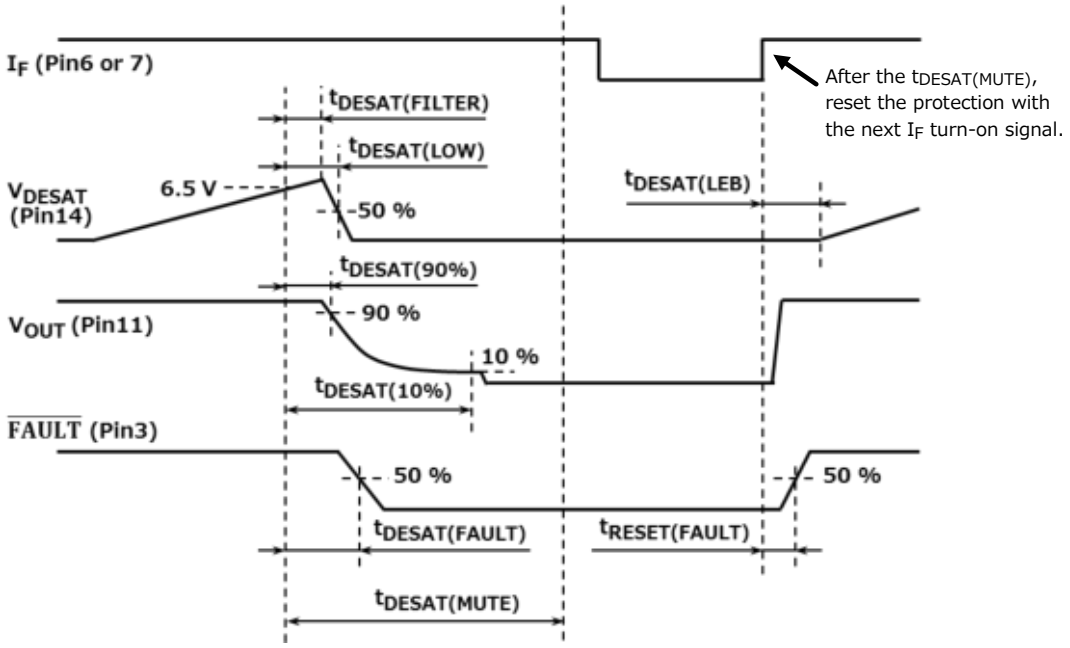


Fig 13.2.2 DESAT fault state timing diagram

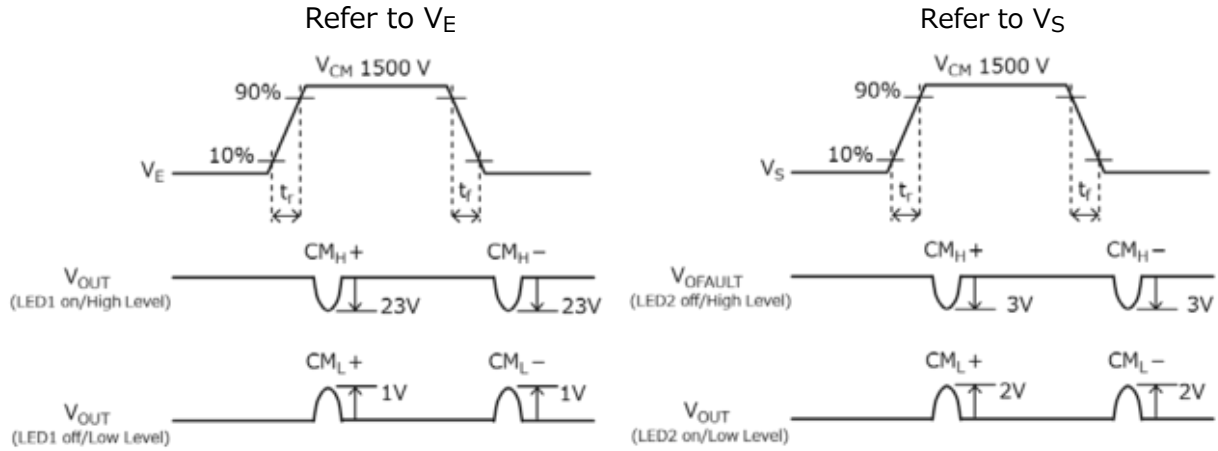


Fig 13.2.3 CMTI waveforms

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13.3. Characteristics Curves (Note)

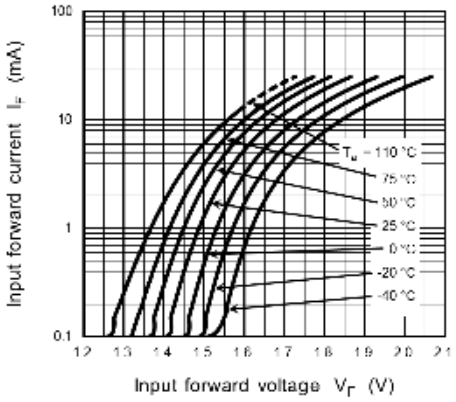


Fig 13.3.1 I_F - V_F

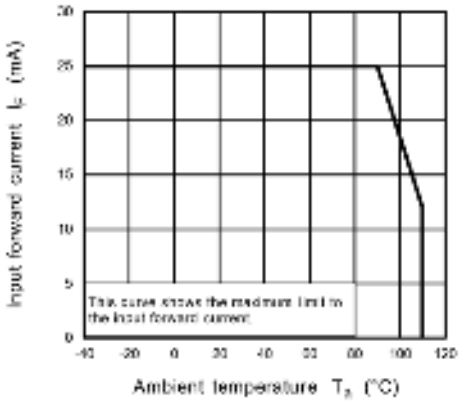


Fig 13.3.2 I_F - T_a

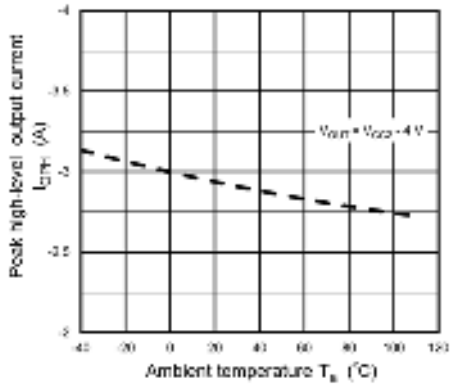


Fig 13.3.3 I_{OPH} - T_a

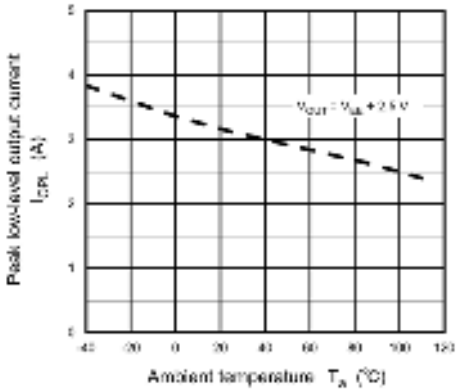


Fig 13.3.4 I_{OPL} - T_a

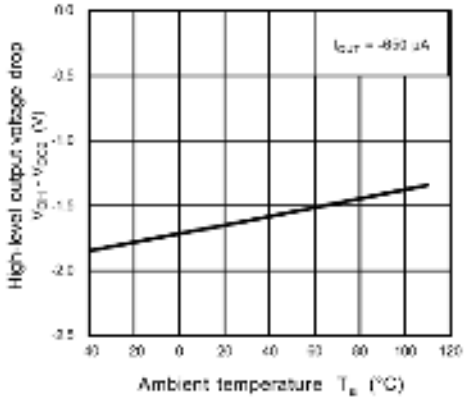


Fig 13.3.5 (V_{OH} - V_{CC2}) - T_a

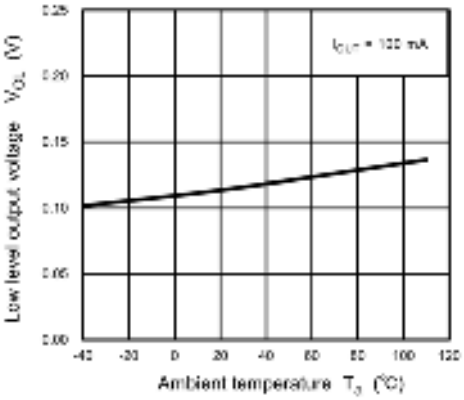


Fig 13.3.6 V_{OL} - T_a

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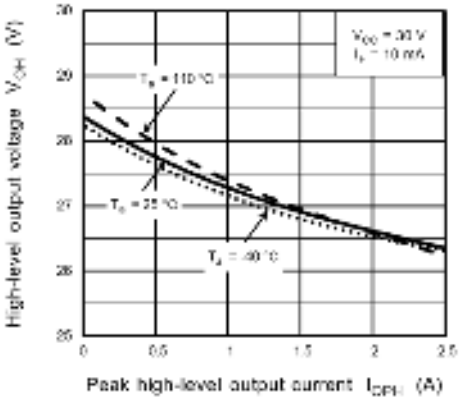


Fig 13.3.7 V_{OH} - I_{OPH}

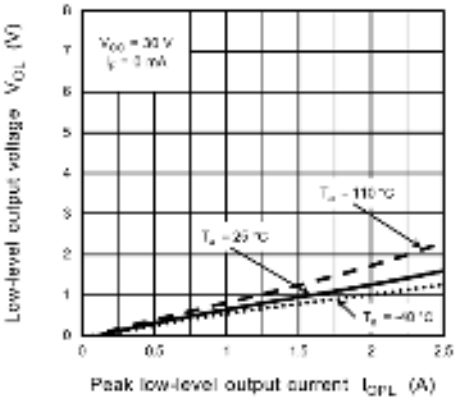


Fig 13.3.8 V_{OL} - I_{OPL}

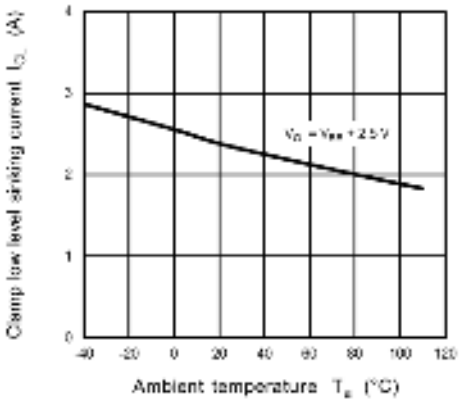


Fig 13.3.9 I_{CL} – T_a

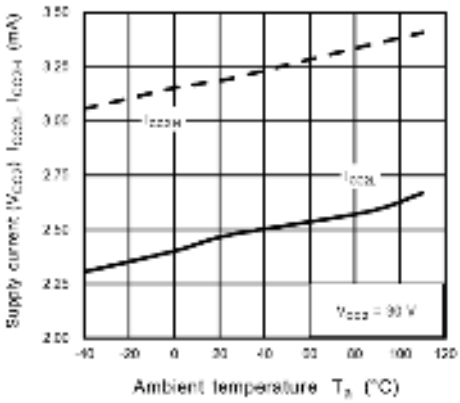


Fig 13.3.10 I_{CC2} – T_a

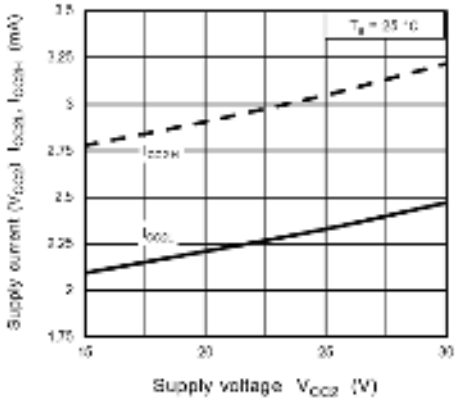


Fig 13.3.11 I_{CC2} - V_{CC2}

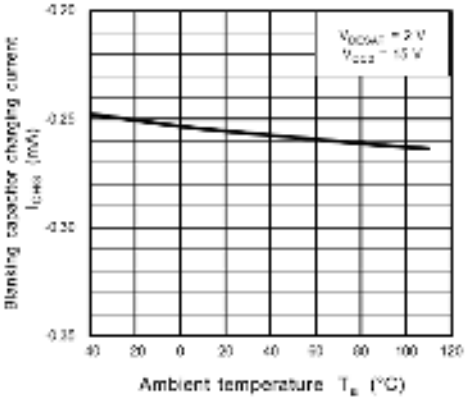


Fig 13.3.12 I_{CHG} - T_a

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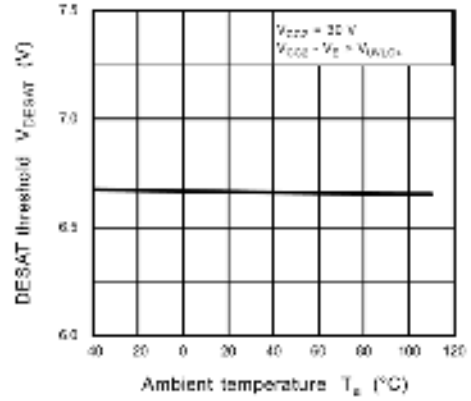


Fig 13.3.13 V_{DESAT} - T_a

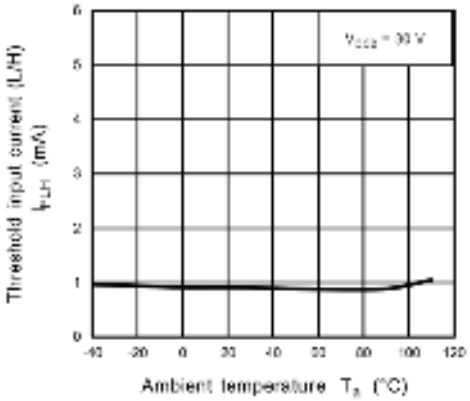


Fig 13.3.14 I_{FLH} - T_a

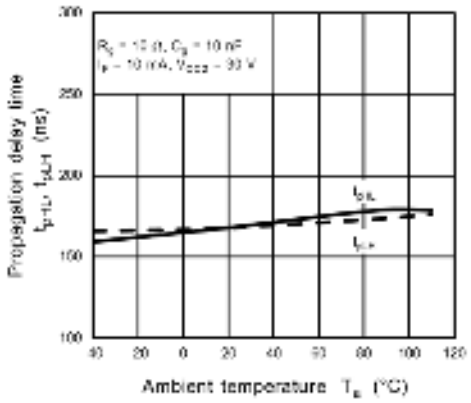


Fig 13.3.15 t_{pLH}, t_{pHL} - T_a

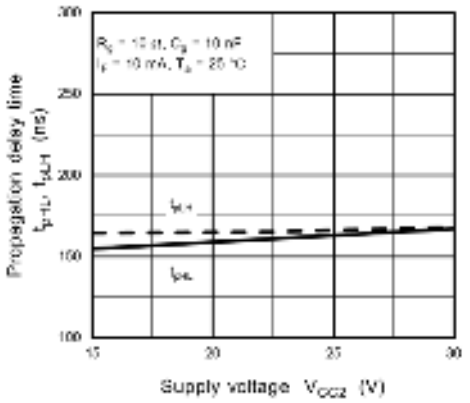


Fig 13.3.16 t_{pLH}, t_{pHL} - V_{CC2}

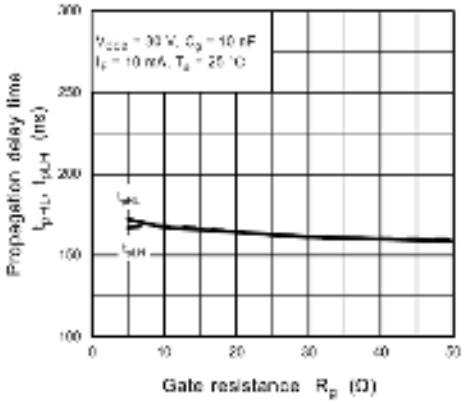


Fig 13.3.17 t_{pLH}, t_{pHL} - R_g

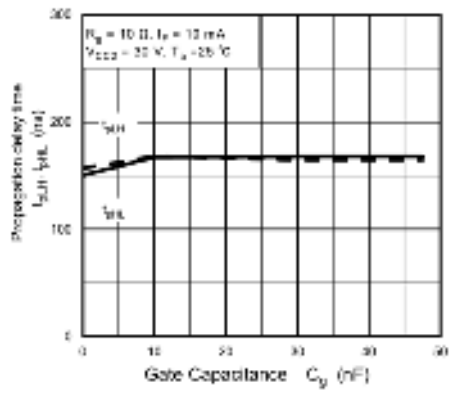


Fig 13.3.18 t_{pLH}, t_{pHL} - C_g

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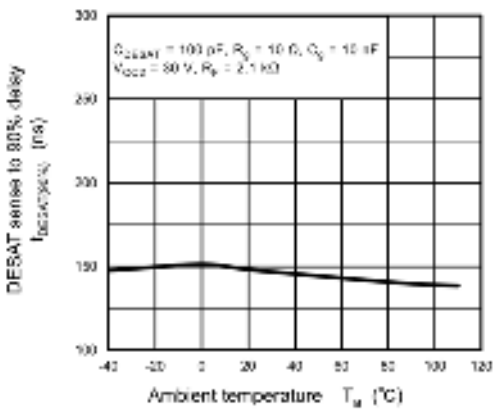


Fig 13.3.19 $t_{DESAT(90\%)}$ - T_a

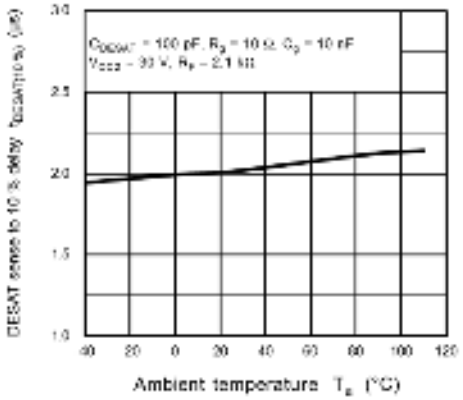


Fig 13.3.20 $t_{DESAT(10\%)}$ - T_a

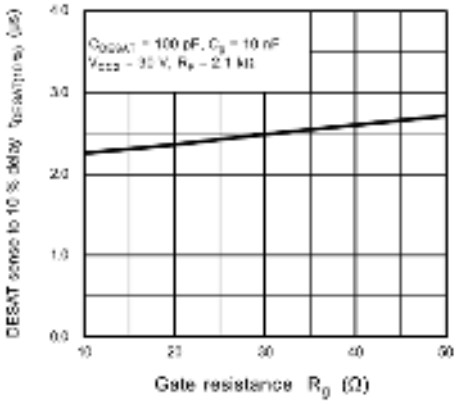


Fig 13.3.21 $t_{DESAT(10\%)}$ - R_g

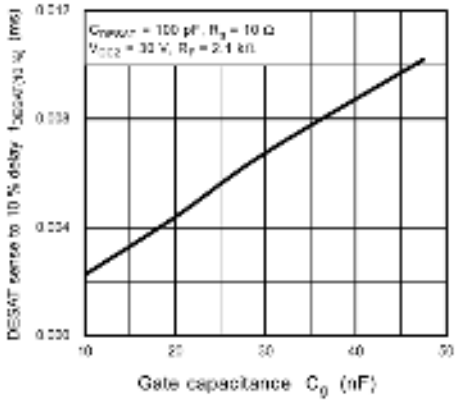


Fig 13.3.22 $t_{DESAT(10\%)}$ - C_g

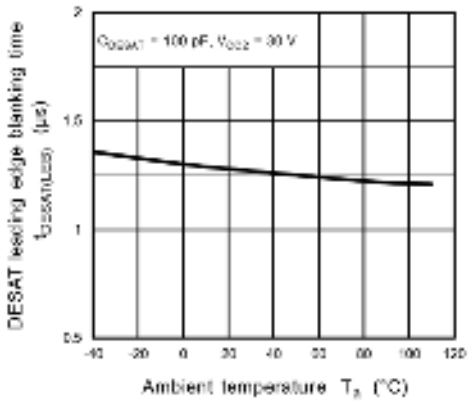


Fig 13.3.23 $t_{DESAT(LEB)}$ - T_a

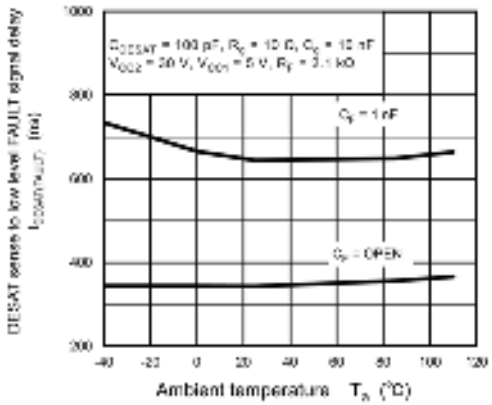


Fig 13.3.24 $t_{DESAT(FAULT)}$ - T_a

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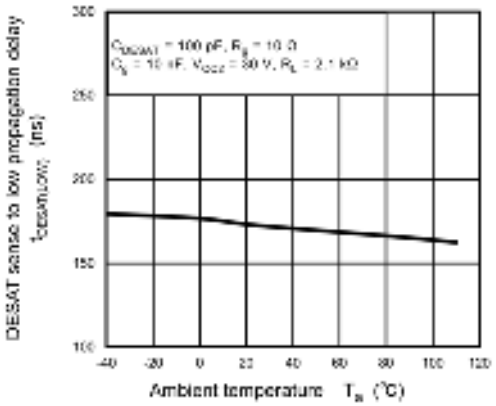


Fig 13.3.25 $t_{DESAT(LOW)}$ - T_a

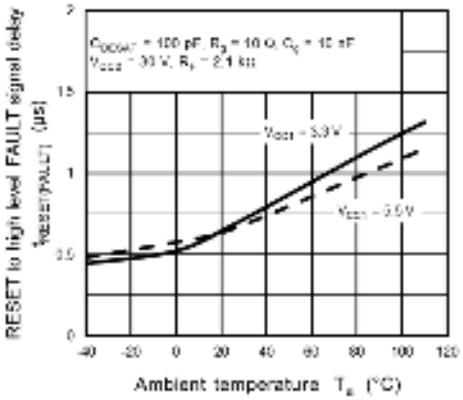


Fig 13.3.26 $t_{RESET(FAULT)}$ - T_a

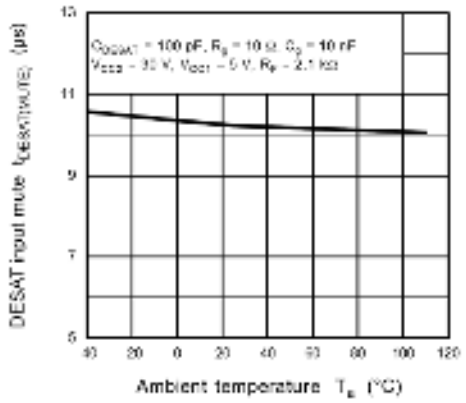


Fig 13.3.27 $t_{DESAT(MUTE)}$ - T_a

Note : The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

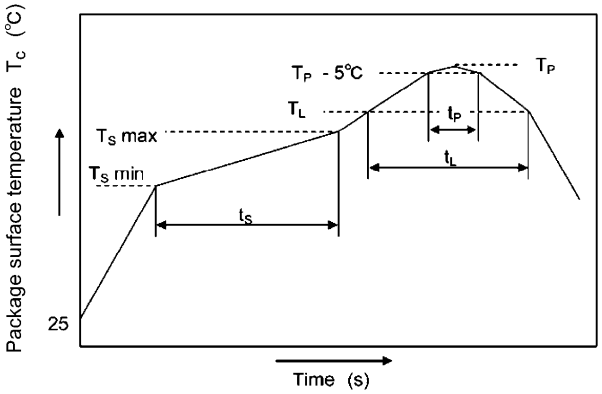
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14. Soldering and Storage

14.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

· When using soldering reflow.
The soldering temperature profile is based on the package surface temperature.
(See the figure shown below, which is based on the package surface temperature.)
Reflow soldering must be performed once or twice.
The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	T_S	150	200	°C
Preheat time	t_S	60	120	s
Ramp-up rate (T_L to T_P)			3	°C/s
Liquidus temperature	T_L	217		°C
Time above T_L	t_L	60	150	s
Peak temperature	T_P		260	°C
Time during which T_c is between (T_P – 5) and T_P	t_P		30	s
Ramp-down rate (T_P to T_L)			6	°C/s

An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

· When using soldering flow
Preheat the device at a temperature of 150℃ (package surface temperature) for 60 to 120 seconds.
Mounting condition of 260℃ within 10 seconds is recommended.
Flow soldering must be performed once.

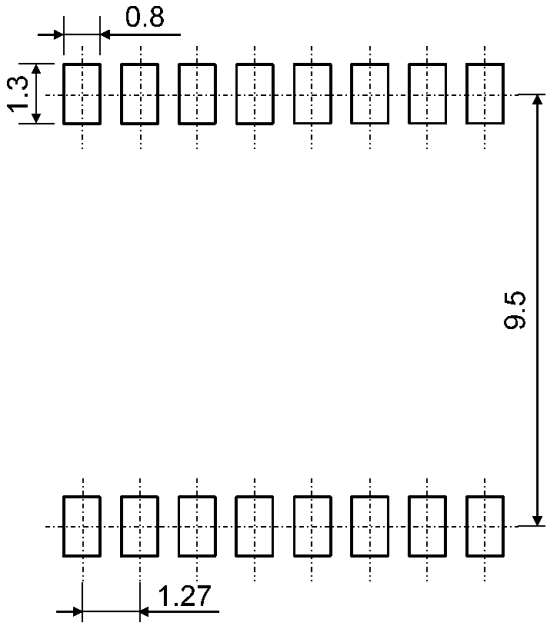
· When using soldering Iron
Complete soldering within 10 seconds for lead temperature not exceeding 260℃ or within 3 seconds not exceeding 350℃.
Heating by soldering iron must be done only once per lead.

14.2. Precautions for General Storage

· Avoid storage locations where devices may be exposed to moisture or direct sunlight.
· Follow the precautions printed on the packing label of the device for transportation and storage.
· Keep the storage location temperature and humidity within a range of 5℃ to 35℃ and 45 % to 75 %, respectively.
· Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
· Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
· When restoring devices after removal from their packing, use anti-static containers.
· Do not allow loads to be applied directly to devices while they are in storage.
· If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

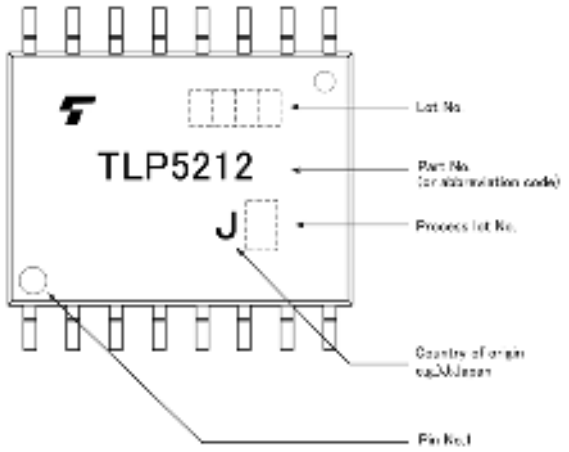
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15. Land Pattern Dimensions (for reference only)



Unit: mm

16. Marking



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17. EN 60747-5-5 Option (D4) Specification

・Part number: TLP5212 **(Note 1)**

・The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN 60747.

Example: TLP5212(D4-TP,E

D4: EN 60747 option

TP: Tape type

E: [[G]]/RoHS COMPATIBLE **(Note 2)**

Note 1: Use TOSHIBA standard type number for safety standard application.
e.g., TLP5212(D4-TP,E → TLP5212

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.
RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification for rated mains voltage ≤ 600 Vrms for rated mains voltage ≤ 1000 Vrms		 I-IV I-III	—
Climatic classification		40 / 110 / 21	—
Pollution degree		2	—
Maximum operating insulation voltage	V_{IORM}	1230	Vpeak
Input to output test voltage, Method A V_{pr} = 1.6 × V_{IORM}, type and sample test t_p = 10 s, partial discharge < 5 pC	V_{pr}	1970	Vpeak
Input to output test voltage, Method B V_{pr} = 1.875 × V_{IORM}, 100 % production test t_p = 1 s, partial discharge < 5 pC	V_{pr}	2310	Vpeak
Highest permissible overvoltage (transient overvoltage, t_{pr} = 60 s)	V_{TR}	8000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I_F, P_{so} = 0) power (output or total power dissipation) temperature	 I_{si} P_{so} T_s	 400 1200 175	 mA mW °C
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	R_{si}	≥ 10^{12} ≥ 10^{11} ≥ 10^{9}	Ω

Fig 17.1 EN 60747 Insulation Characteristics

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Minimum creepage distance	Cr	8.0 mm
Minimum clearance	Cl	8.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	500

Fig 17.2 Insulation Related Specifications (Note)

Note: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

Fig 17.3 Marking on Packing for EN 60747

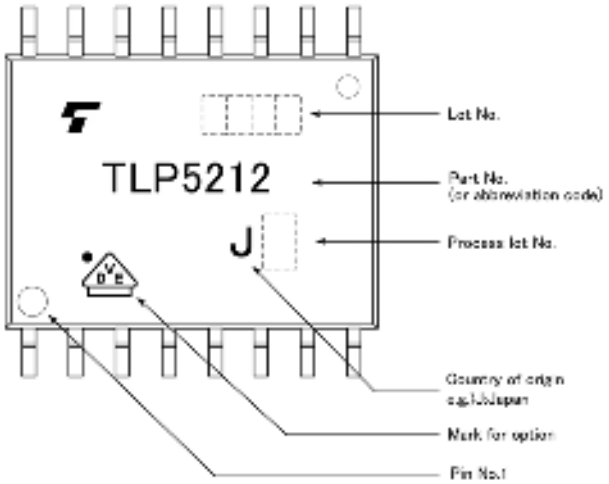


Fig 17.4 Marking Example (Note)

Note: The above marking is applied to the photo couplers that have been qualified according to option (D4) of EN 60747.

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Figure 1 Partial discharge measurement procedure according to EN 60747
Destructive test for qualification and sampling tests.

Method A

(for type and sampling tests, destructive tests)

t_1, t_2	= 1 to 10 s
t_3, t_4	= 1 s
t_p (Measuring time for partial discharge)	= 10 s
t_b	= 12 s
t_{ini}	= 60 s

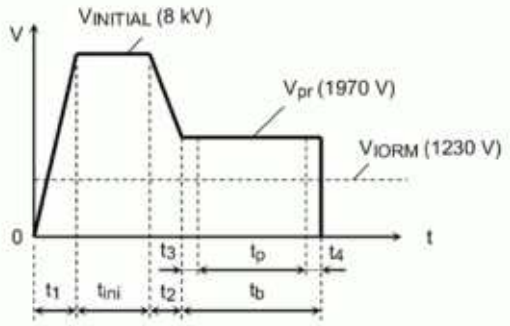


Figure 2 Partial discharge measurement procedure according to EN 60747
Non-destructive test for 100 % inspection.

Method B

(for sample test, non-destructive test)

t_3, t_4	= 0.1 s
t_p (Measuring time for partial discharge)	= 1 s
t_b	= 1.2 s

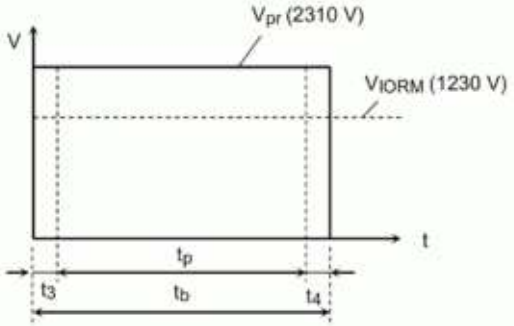


Figure 3 Dependency of maximum safety ratings on ambient temperature

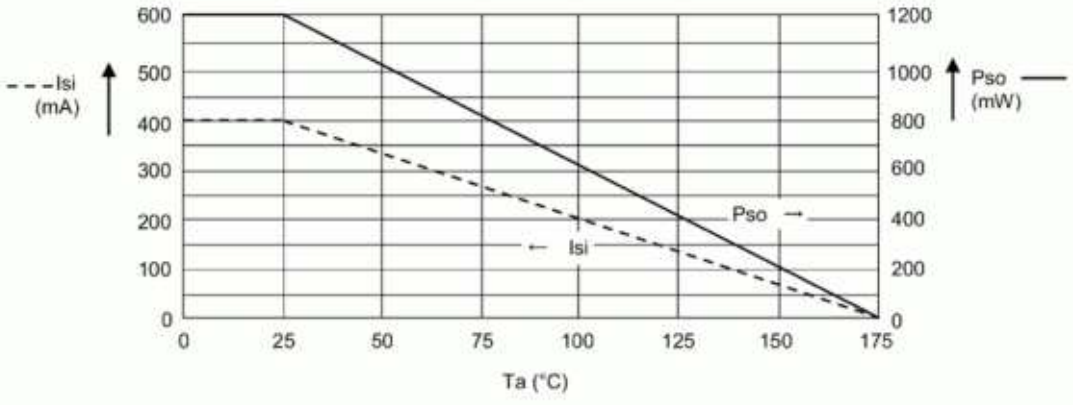


Fig 17.5 Measurement Procedure

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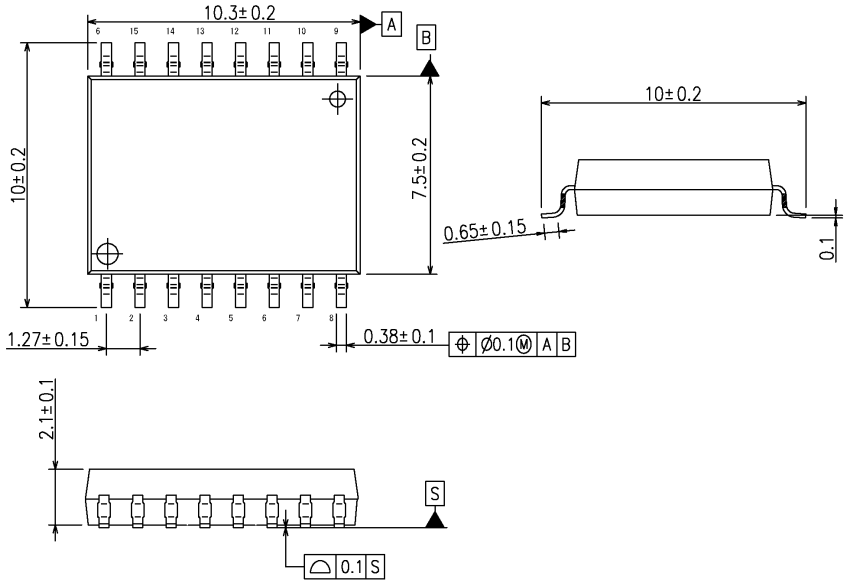
18. Ordering Information (Example of Item Name)

Item Name	VDE Option	Packing (MOQ)
TLP5212(E		Magazine (50 pcs)
TLP5212(TP,E		Tape and reel (1500 pcs)
TLP5212(D4,E	EN 60747-5-5	Magazine (50 pcs)
TLP5212(D4-TP,E	EN 60747-5-5	Tape and reel (1500 pcs)

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Package Dimensions

Unit: mm



Weight: 0.364 g (typ.)

Package Name(s)
TOSHIBA: 11-10M1

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